

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A coating carried by a substrate having a surface, comprising, from the substrate surface outwardly:

- a) an inner dielectric layer;
- b) a first infrared reflective layer;
- c) an intermediate dielectric stack comprising alternating layers of a first dielectric and a second dielectric, wherein the intermediate dielectric stack includes, moving outwardly, a first intermediate dielectric layer of said first dielectric, a second intermediate dielectric layer of said second dielectric, a third intermediate dielectric layer of said first dielectric, a fourth intermediate dielectric layer of said second dielectric, and a fifth intermediate dielectric layer of said first dielectric, wherein each of the first, third, and fifth intermediate dielectric layers has an optical thickness greater than the optical thickness of any of the second and fourth intermediate dielectric layers, each intermediate dielectric layer having a physical thickness of no more than about 250Å, wherein the first dielectric comprises an oxide or suboxide and the second dielectric comprises silicon nitride;
- d) a second infrared reflective layer; and
- e) an outer dielectric layer.

2. (Cancelled)

3. (Currently Amended) The coating of claim 1 wherein the first, third, and fifth intermediate dielectric layers comprise an oxide of the same metal, ~~and wherein the second and fourth intermediate dielectric layers comprise a nitride of the same metal.~~

4. (Cancelled)

5. (Currently Amended) The coating of claim 1 wherein said first dielectric comprises an oxide or suboxide of a metal comprising zinc, indium, tin, bismuth or an alloy of zinc, indium, tin or bismuth, ~~and said second dielectric comprises a nitride of a metal that is different from said metal of said first dielectric.~~

6. (Currently Amended) The coating of claim 1 wherein said first dielectric comprises an oxide or suboxide of zinc ~~and the second dielectric comprises silicon nitride.~~

7. (Original) The coating of claim 1 wherein said first dielectric is polycrystalline and said second dielectric is substantially amorphous.

8. (Original) The coating of claim 1 including a layer comprising niobium between the first infrared reflective layer and the intermediate dielectric stack, and a layer comprising niobium between second infrared reflective layer and the outer dielectric layer.

9. (Previously Presented) The coating of claim 1 wherein said second intermediate dielectric layer is contiguous to said first intermediate dielectric layer, said third intermediate dielectric layer is contiguous to said second intermediate layer, said fourth intermediate dielectric layer is contiguous to said third intermediate dielectric layer, and said fifth intermediate dielectric layer is contiguous to said fourth intermediate dielectric layer.

10. (Cancelled)

11. (Currently Amended) A method of forming a coated glass article, the method comprising:

- a) providing a glass substrate;
- b) depositing a coating on the glass substrate by:
 - i) depositing an inner dielectric layer;
 - ii) thereafter, depositing a first infrared reflective layer;
 - iii) thereafter, depositing an intermediate dielectric stack by depositing alternating layers of a first dielectric and a second dielectric, wherein the intermediate dielectric stack includes, moving outwardly, a first intermediate dielectric layer of said first dielectric, a second intermediate dielectric layer of said second dielectric, a third intermediate dielectric layer of said first dielectric, a fourth intermediate dielectric layer of said second dielectric, and a fifth intermediate dielectric layer of said first dielectric, wherein each of the first, third, and fifth intermediate dielectric layers has an optical thickness greater than the optical thickness of any of the second and fourth intermediate dielectric layers, each intermediate dielectric layer having a physical thickness of no more than about 250Å, wherein the first dielectric comprises an oxide or suboxide and the second dielectric comprises silicon nitride;
 - iv) thereafter, depositing a second infrared reflective layer; and
 - v) thereafter, depositing an outer dielectric layer.

12. (Cancelled)

13. (Currently Amended) The method of claim 11 wherein the first, third, and fifth intermediate dielectric layers are all deposited as film comprising an oxide of the same metal, ~~and wherein the second and fourth intermediate dielectric layers are both deposited as film comprising a nitride of the same metal.~~

14. (Cancelled)

15. (Currently Amended) The method of claim 11 wherein said first dielectric comprises an oxide or suboxide of a metal comprising zinc, indium, tin, bismuth or an alloy of zinc, indium, tin or bismuth, ~~and said second dielectric comprises a nitride of a metal different from said metal of said first dielectric.~~

16. (Currently Amended) The method of claim 11 wherein said first dielectric comprises an oxide or suboxide of zinc ~~and the second dielectric comprises silicon nitride.~~

17. (Original) The method of claim 11 wherein said first dielectric is polycrystalline and said second dielectric is substantially amorphous.

18. (Original) The method of claim 11 including depositing a layer comprising niobium between the first infrared reflective layer and the intermediate dielectric stack, and depositing a layer comprising niobium between second infrared reflective layer and the outer dielectric layer.

19. (Original) The method of claim 11 wherein said second intermediate dielectric layers is deposited directly upon said first intermediate dielectric layer, said third intermediate dielectric layers is deposited directly upon said second intermediate layer, said fourth intermediate dielectric layer is deposited directly upon said third intermediate dielectric layer, and said fifth intermediate dielectric layer is deposited directly upon said fourth intermediate dielectric layer.

20. (Original) The method of claim 11 wherein said coating is deposited by sputtering.

21. (Cancelled)

22. (Cancelled)

23. (Cancelled)

24. (New) The coating of claim 1 wherein each of the intermediate dielectric layers has a physical thickness of no more than about 22.5 nm.